Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in an MLPAK33 (SOT8002) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Ultra low Q_G and Q_{GD} for high system efficiency, especially at higher switching frequencies
- Superfast switching with soft-recovery
- · Low spiking and ringing for low EMI designs
- MLPAK33 package (3.3 x 3.3 mm footprint)

3. Applications

- DC to DC conversion
- · Battery management
- Low-side load switch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|---------------------|--|---|-----|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | 30 | V |
| V_{GS} | gate-source voltage | | | -20 | - | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | - | 21.5 | Α |
| Static charac | teristics | | | | | | · |
| R _{DSon} | R _{DSon} drain-source on-state resistance | V _{GS} = 10 V; I _D = 12.7 A; T _j = 25 °C | | - | 5.7 | 6.7 | mΩ |
| | | V_{GS} = 4.5 V; I_D = 11.2 A; T_j = 25 °C | | - | 6.9 | 8.6 | mΩ |
| Dynamic cha | racteristics | | | | | | · |
| Q _{G(tot)} | total gate charge | V_{DS} = 15 V; I_{D} = 11.2 A; V_{GS} = 4.5 V; T_{j} = 25 °C | | - | 7.9 | 11.9 | nC |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².



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5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|---------------------|----------------|
| 1 | S | source | 1 2 3 4 | D |
| 2 | S | source | | |
| 3 | S | source | | G—(F) |
| 4 | G | gate | l h d | mbb076 S |
| 5 | D | drain | | |
| 6 | D | drain | | |
| 7 | D | drain | MLPAK33 (SOT8002-1) | |
| 8 | D | drain | | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | | | | |
|-------------|---------|---|-----------|--|--|--|--|--|
| | Name | Description | Version | | | | | |
| PXN6R7-30QL | | plastic thermal enhanced surface mounted package; mini leads; 8 terminals; pitch 0.65 mm; 3.3 x 3.3 x 0.8 mm body | SOT8002-1 | | | | | |

7. Marking

Table 4. Marking codes

| Type number | Marking code |
|-------------|--------------|
| PXN6R7-30QL | 9AF |

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|----------------------|--|--|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | 30 | V |
| V _{GS} | gate-source voltage | | | -20 | 20 | V |
| I _D | drain current | V _{GS} = 10 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 21.5 | Α |
| | | V _{GS} = 10 V; T _{amb} = 25 °C | [1] | - | 12.7 | Α |
| | | V _{GS} = 10 V; T _{amb} = 100 °C | [1] | - | 8 | Α |
| | | V _{GS} = 10 V; T _{sp} = 25 °C | | - | 62 | Α |
| I _{DM} | peak drain current | T _{amb} = 25 °C; single pulse; t _p ≤ 10 μs | | - | 87 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C; t ≤ 5 s | [1] | - | 4.8 | W |
| | | T _{amb} = 25 °C | [1] | - | 1.7 | W |
| | | T _{sp} = 25 °C | | - | 40.3 | W |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain | diode | | | l | | |
| I _S | source current | T _{amb} = 25 °C | [1] | - | 1.5 | Α |
| Avalanche ru | iggedness | - | | 1 | | |
| E _{DS(AL)S} | non-repetitive drain- source avalanche energy | $T_{j(init)}$ = 25 °C; I_D = 2.3 A; DUT in avalanche (unclamped) | | - | 34.5 | mJ |

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and mounting pad for drain 6 cm².

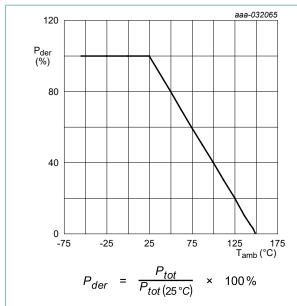


Fig. 1. Normalized total power dissipation as a function of ambient temperature

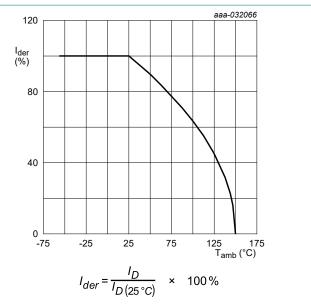


Fig. 2. Normalized continous drain current as a function of ambient temperature

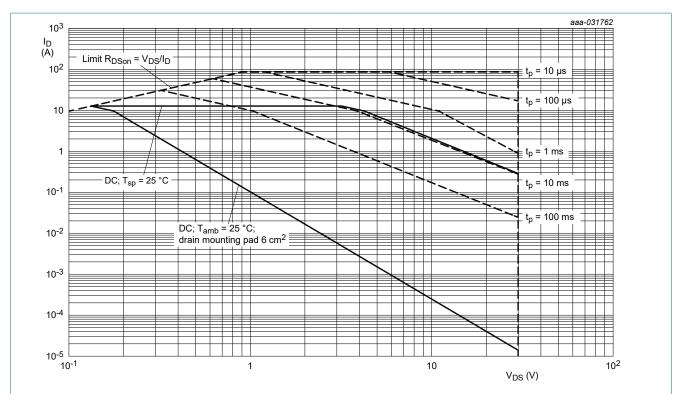


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

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9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance from | in free air | [1] | - | 150 | 190 | K/W |
| | junction to ambient | | [2] | - | 60 | 75 | K/W |
| | | in free air; t ≤ 5 s | [2] | - | 21 | 26 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 2.1 | 3.1 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and mounting pad for drain 6 cm².

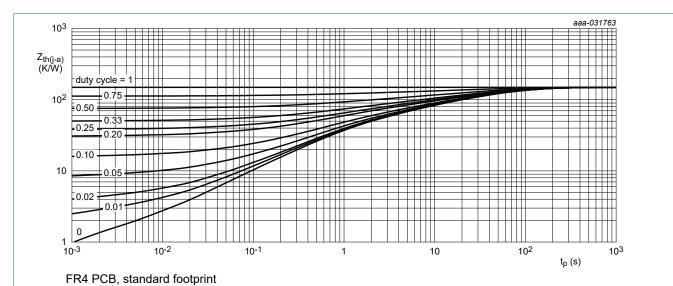


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

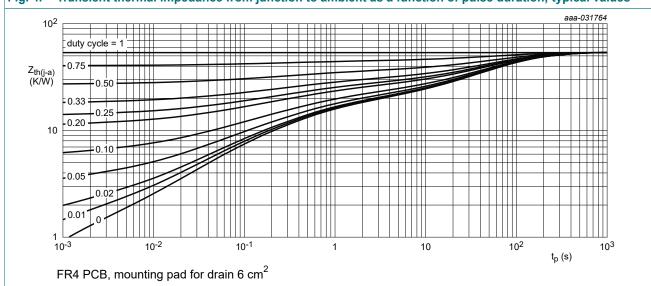


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, N-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|------------------------|---------------------------------------|---|-----|------|------|------|
| Static chara | acteristics | | | | | |
| V _{(BR)DSS} | drain-source breakdown voltage | I _D = 250 μA; V _{GS} = 0 V; T _j = 25 °C | 30 | - | - | V |
| V_{GSth} | gate-source threshold voltage | $I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$ | 1.2 | 1.7 | 2.2 | V |
| I _{DSS} | drain leakage current | $V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 1 | μΑ |
| I _{GSS} | gate leakage current | $V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$ | - | - | 100 | nA |
| | | V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state | $V_{GS} = 10 \text{ V}; I_D = 12.7 \text{ A}; T_j = 25 \text{ °C}$ | - | 5.7 | 6.7 | mΩ |
| | resistance | V _{GS} = 10 V; I _D = 12.7 A; T _j = 150 °C | - | 8.8 | 10.4 | mΩ |
| | | $V_{GS} = 4.5 \text{ V}; I_D = 11.2 \text{ A}; T_j = 25 ^{\circ}\text{C}$ | - | 6.9 | 8.6 | mΩ |
| g _{fs} | forward transconductance | $V_{DS} = 10 \text{ V}; I_D = 12.7 \text{ A}; T_j = 25 \text{ °C}$ | - | 33 | - | S |
| R _G | gate resistance | f = 1 MHz | - | 1.2 | - | Ω |
| Dynamic ch | naracteristics | | | | ' | |
| Q _{G(tot)} | total gate charge | V_{DS} = 15 V; I_{D} = 12.7 A; V_{GS} = 10 V; I_{j} = 25 °C | - | 16.5 | 24.8 | nC |
| | | V _{DS} = 15 V; I _D = 11.2 A; V _{GS} = 4.5 V; | - | 7.9 | 11.9 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 2.8 | - | nC |
| Q _{GS(th)} | pre-threshold gate- source charge | | - | 1.7 | - | nC |
| Q _{GS(th-pl)} | post-threshold gate- source charge | | - | 1.1 | - | nC |
| Q _{GD} | gate-drain charge | 1 | - | 2.1 | - | nC |
| V_{GSpl} | gate-source plateau voltage | $V_{DS} = 15 \text{ V}; I_D = 11.2 \text{ A}; T_j = 25 \text{ °C}$ | - | 2.6 | - | V |
| C _{iss} | input capacitance | V _{DS} = 15 V; f = 1 MHz; V _{GS} = 0 V; | - | 1150 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 380 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 66 | - | pF |
| t _{d(on)} | turn-on delay time | V _{DS} = 15 V; I _D = 11.2 A; V _{GS} = 4.5 V; | - | 5 | - | ns |
| t _r | rise time | $R_{G(ext)} = 5 \Omega$; $T_j = 25 °C$ | - | 8 | - | ns |
| $t_{d(off)}$ | turn-off delay time | 1 | - | 6 | - | ns |
| t _f | fall time | 1 | - | 3 | - | ns |
| Source-dra | in diode | | | | | |
| V _{SD} | source-drain voltage | I _S = 1.5 A; V _{GS} = 0 V; T _j = 25 °C | - | 0.7 | 1.2 | V |
| t _{rr} | reverse recovery time | I _S = 1.5 A; dI _S /dt = -100 A/μs; | - | 15 | - | ns |
| Q _r | recovered charge | $V_{GS} = 4.5 \text{ V}; V_{DS} = 15 \text{ V}; T_j = 25 \text{ °C}$ | - | 6 | - | nC |
| t _a | reverse recovery rise time | | - | 8 | - | ns |
| t _b | reverse recovery fall time | 1 | - | 7 | - | ns |

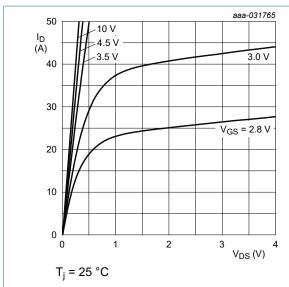


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

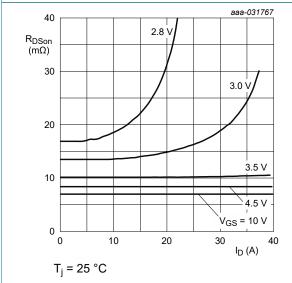


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

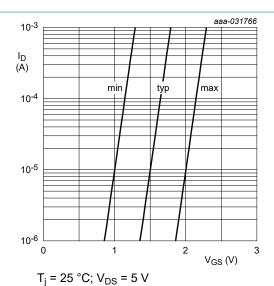


Fig. 7. Subthreshold drain current as a function of gate-source voltage

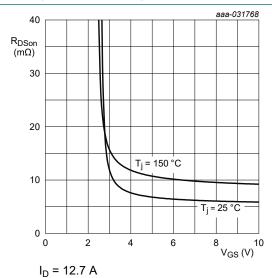


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

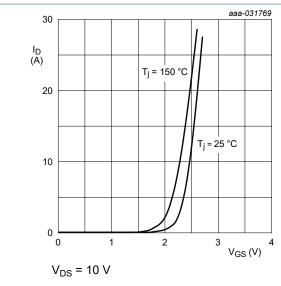


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

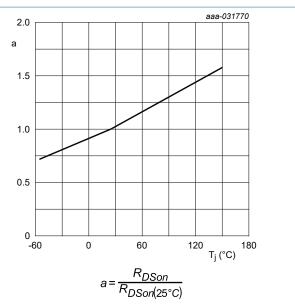


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

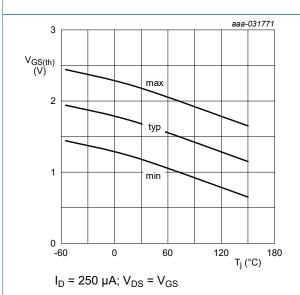


Fig. 12. Gate-source threshold voltage as a function of junction temperature

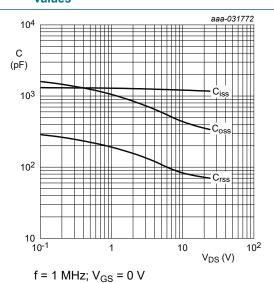


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

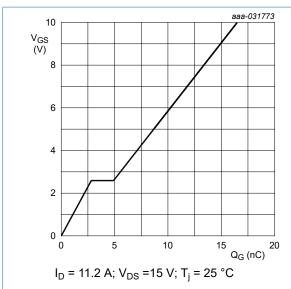


Fig. 14. Gate-source voltage as a function of gate charge; typical values

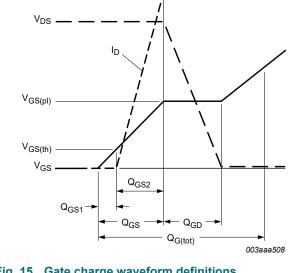


Fig. 15. Gate charge waveform definitions

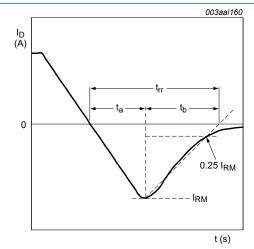


Fig. 16. Reverse recovery timing definition

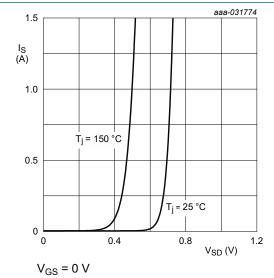
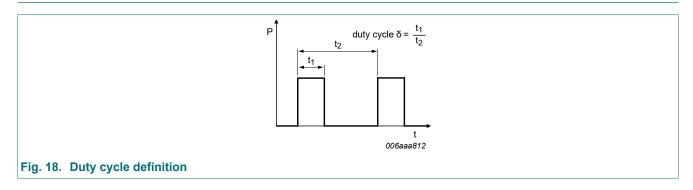


Fig. 17. Source current as a function of source-drain voltage; typical values

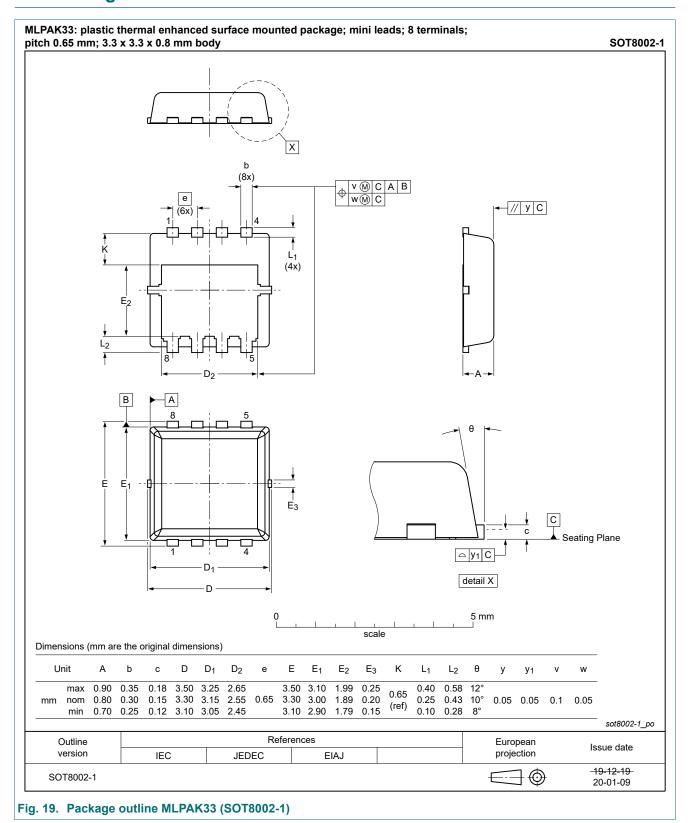
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11. Test information



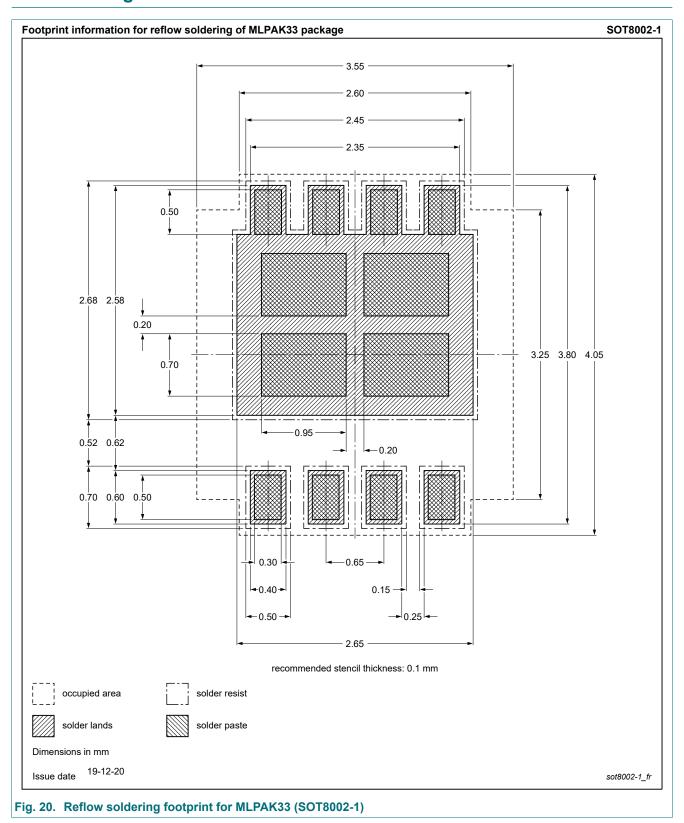
30 V, N-channel Trench MOSFET

12. Package outline



30 V, N-channel Trench MOSFET

13. Soldering



30 V, N-channel Trench MOSFET

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|-----------------|--------------|--------------------|---------------|------------|
| PXN6R7-30QL v.1 | 20201102 | Product data sheet | - | - |

30 V, N-channel Trench MOSFET

15. Legal information

Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|---------------------------------|-----------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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